

Advanced Power MOSFET

IRF720A

FEATURES

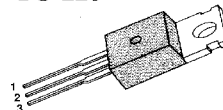
- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Lower Leakage Current : $10\mu\text{A}$ (Max.) @ $V_{\text{DS}} = 400\text{V}$
- Lower $R_{\text{DS(ON)}}$: 1.408Ω (Typ.)

$$BV_{\text{DSS}} = 400\text{ V}$$

$$R_{\text{DS(on)}} = 1.8\Omega$$

$$I_{\text{D}} = 3.3\text{ A}$$

TO-220



1. Gate 2. Drain 3. Source

Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
V_{DSS}	Drain-to-Source Voltage	400	V
I_{D}	Continuous Drain Current ($T_{\text{C}}=25^{\circ}\text{C}$)	3.3	A
	Continuous Drain Current ($T_{\text{C}}=100^{\circ}\text{C}$)	2.1	
I_{DM}	Drain Current-Pulsed ①	13	A
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy ②	249	mJ
I_{AR}	Avalanche Current ①	3.3	A
E_{AR}	Repetitive Avalanche Energy ①	4.9	mJ
dv/dt	Peak Diode Recovery dv/dt ③	4.0	V/ns
P_{D}	Total Power Dissipation ($T_{\text{C}}=25^{\circ}\text{C}$)	49	W
	Linear Derating Factor	0.39	W/ $^{\circ}\text{C}$
$T_{\text{J}}, T_{\text{STG}}$	Operating Junction and Storage Temperature Range	- 55 to +150	$^{\circ}\text{C}$
T_{L}	Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5-seconds	300	

Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta\text{JC}}$	Junction-to-Case	--	2.57	$^{\circ}\text{C/W}$
$R_{\theta\text{CS}}$	Case-to-Sink	0.5	--	
$R_{\theta\text{JA}}$	Junction-to-Ambient	--	62.5	

SAMSUNG

ELECTRONICS

IRF720A

N-CHANNEL POWER MOSFET

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
BV_{DSS}	Drain-Source Breakdown Voltage	400	--	--	V	$V_{GS}=0V, I_D=250\mu A$
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	0.54	--	V/ $^\circ\text{C}$	$I_D=250\mu A$ See Fig 7
$V_{GS(th)}$	Gate Threshold Voltage	2.0	--	4.0	V	$V_{DS}=5V, I_D=250\mu A$
I_{GSS}	Gate-Source Leakage, Forward	--	--	100	nA	$V_{GS}=30V$
	Gate-Source Leakage, Reverse	--	--	-100		$V_{GS}=-30V$
I_{DSS}	Drain-to-Source Leakage Current	--	--	10	μA	$V_{DS}=400V$
		--	--	100		$V_{DS}=320V, T_C=125^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	1.8	Ω	$V_{GS}=10V, I_D=1.65A$ ④
g_{fs}	Forward Transconductance	--	2.25	--	S	$V_{DS}=50V, I_D=1.65A$ ④
C_{iss}	Input Capacitance	--	385	500	pF	$V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$ See Fig 5
C_{oss}	Output Capacitance	--	60	70		
C_{rss}	Reverse Transfer Capacitance	--	27	33		
$t_{d(on)}$	Turn-On Delay Time	--	12	35	ns	$V_{DD}=200V, I_D=3.3A,$ $R_G=18\Omega$ See Fig 13 ④ ⑤
t_r	Rise Time	--	17	45		
$t_{d(off)}$	Turn-Off Delay Time	--	51	110		
t_f	Fall Time	--	18	45		
Q_g	Total Gate Charge	--	19	26	nC	$V_{DS}=320V, V_{GS}=10V,$ $I_D=3.3A$ See Fig 6 & Fig 12 ④ ⑤
Q_{gs}	Gate-Source Charge	--	2.7	--		
Q_{gd}	Gate-Drain("Miller") Charge	--	11.1	--		

Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
I_S	Continuous Source Current	--	--	3.3	A	Integral reverse pn-diode in the MOSFET
I_{SM}	Pulsed-Source Current ①	--	--	13		
V_{SD}	Diode Forward Voltage ④	--	--	1.5	V	$T_J=25^\circ\text{C}, I_S=3.3A, V_{GS}=0V$
t_{rr}	Reverse Recovery Time	--	230	--	ns	$T_J=25^\circ\text{C}, I_F=3.3A$
Q_{rr}	Reverse Recovery Charge	--	1.16	--	μC	$di_F/dt=100A/\mu\text{s}$

Notes ;

- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ② $L=40\text{mH}, I_{AS}=3.3A, V_{DD}=50V, R_G=27\Omega$, Starting $T_J=25^\circ\text{C}$
- ③ $I_{SD} \leq 3.3A, di/dt \leq 110A/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$
- ④ Pulse Test : Pulse Width = 250 μs , Duty Cycle $\leq 2\%$
- ⑤ Essentially Independent of Operating Temperature

Fig 1. Output Characteristics

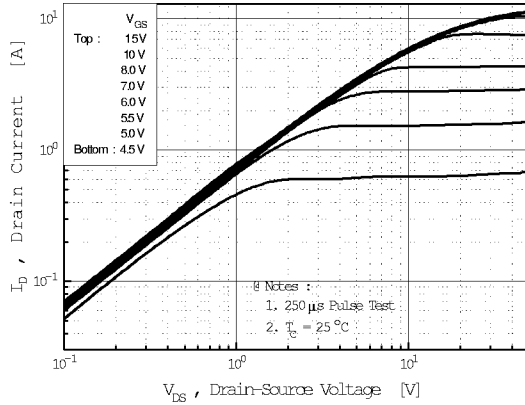


Fig 2. Transfer Characteristics

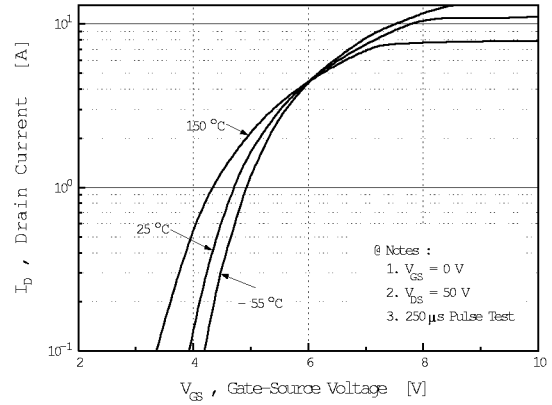


Fig 3. On-Resistance vs. Drain Current

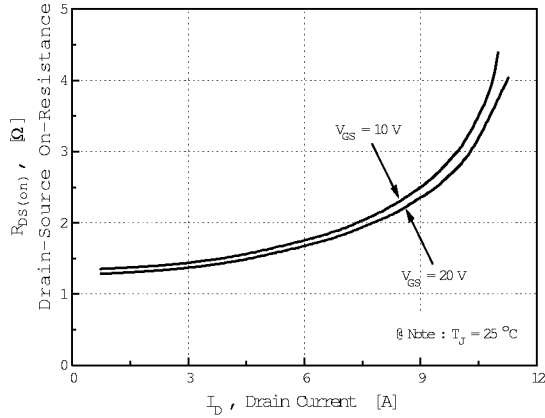


Fig 4. Source-Drain Diode Forward Voltage

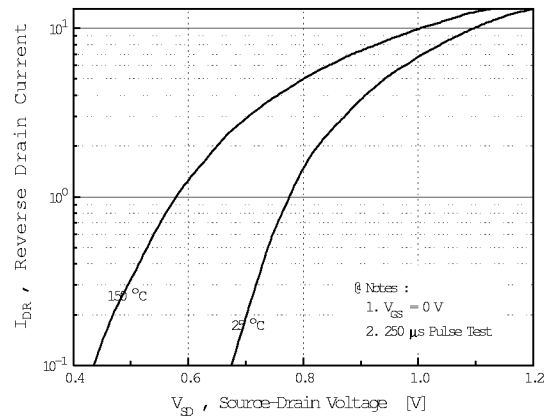


Fig 5. Capacitance vs. Drain-Source Voltage

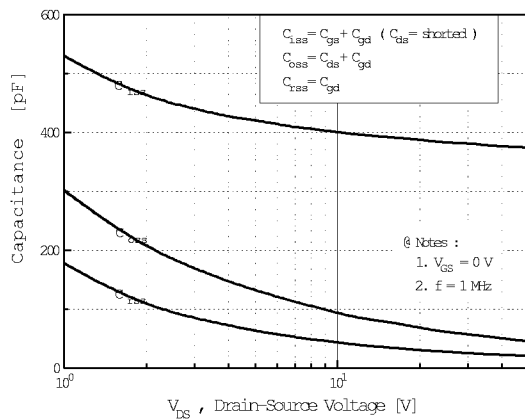
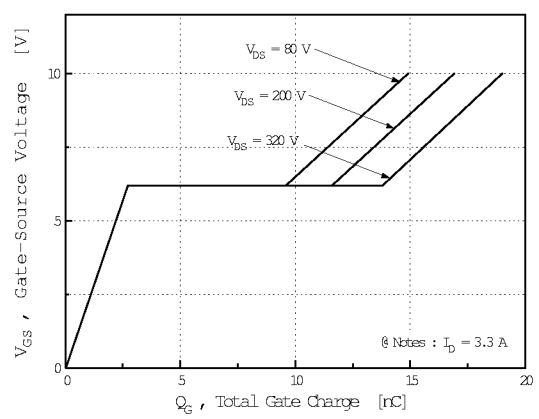


Fig 6. Gate Charge vs. Gate-Source Voltage



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N-CHANNEL POWER MOSFET

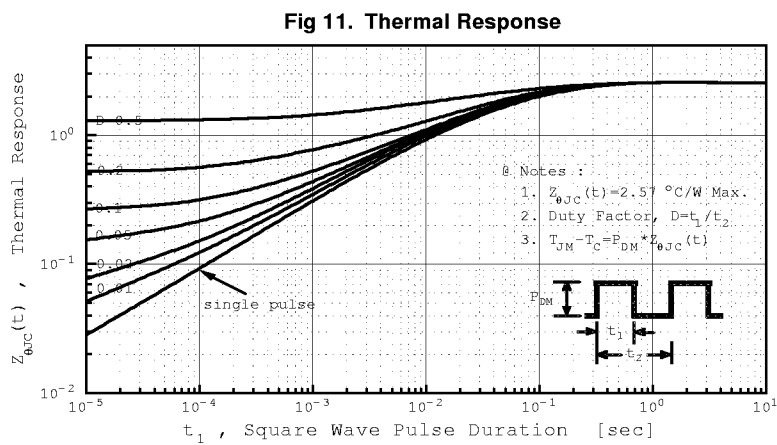
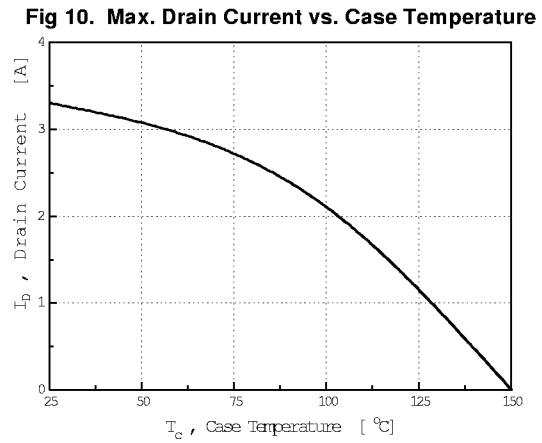
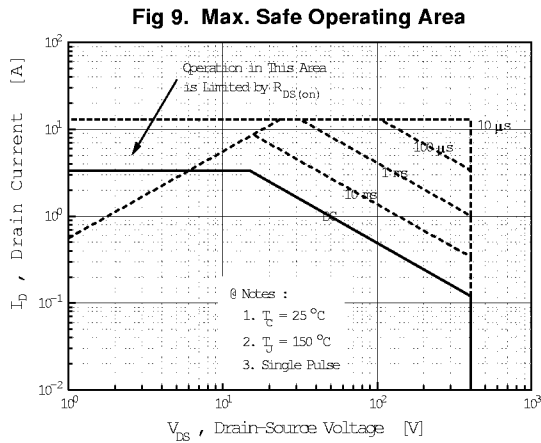
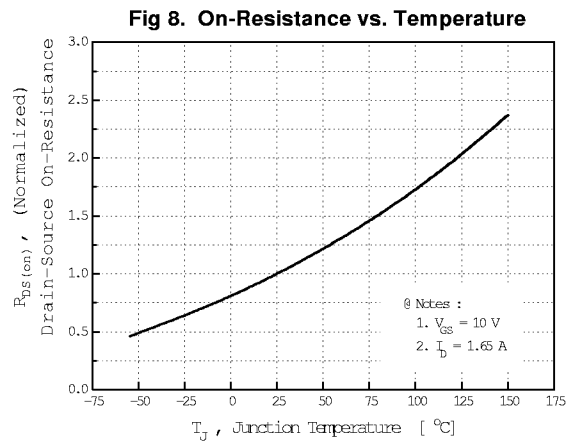
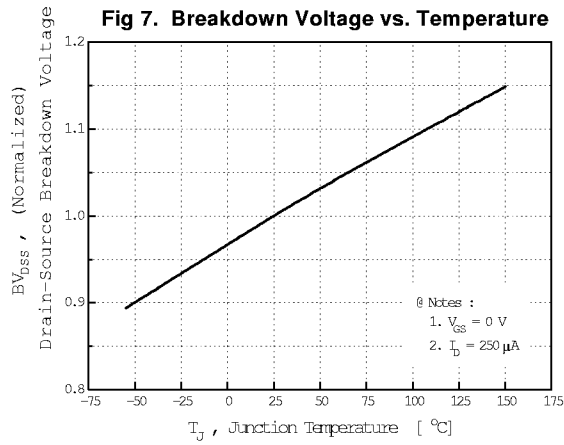


Fig 12. Gate Charge Test Circuit & Waveform

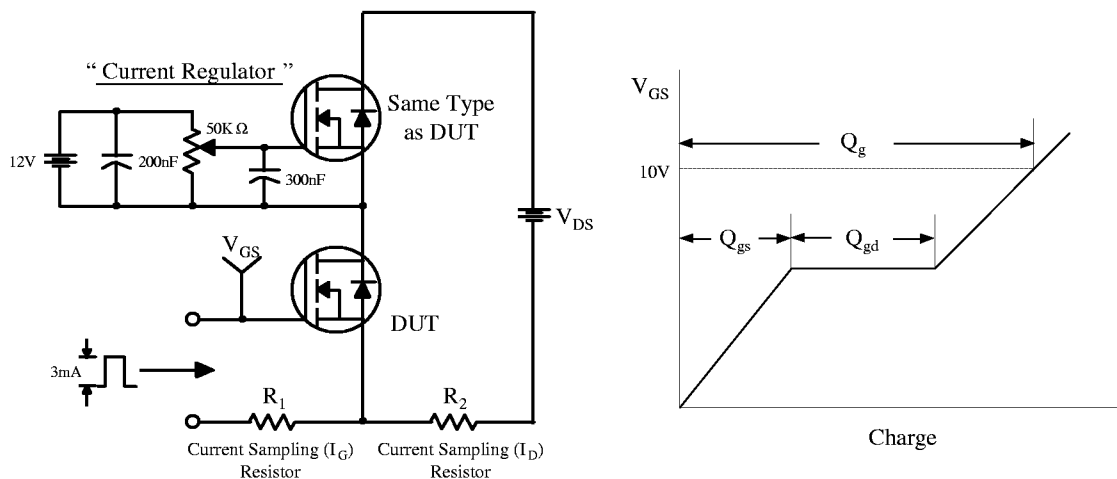


Fig 13. Resistive Switching Test Circuit & Waveforms

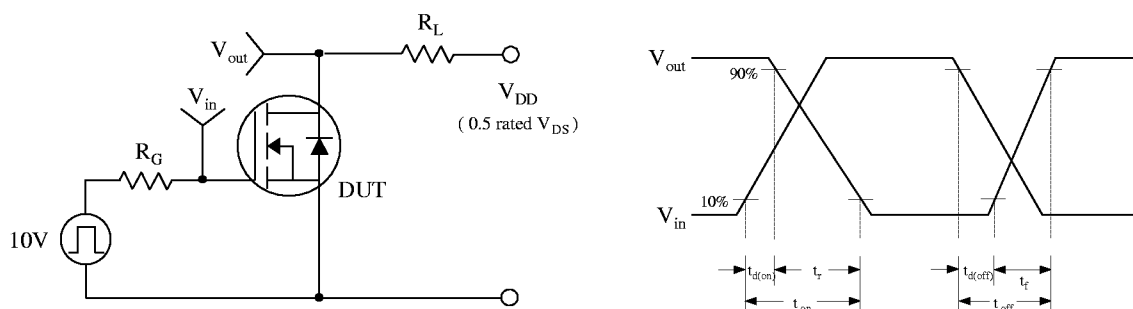


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

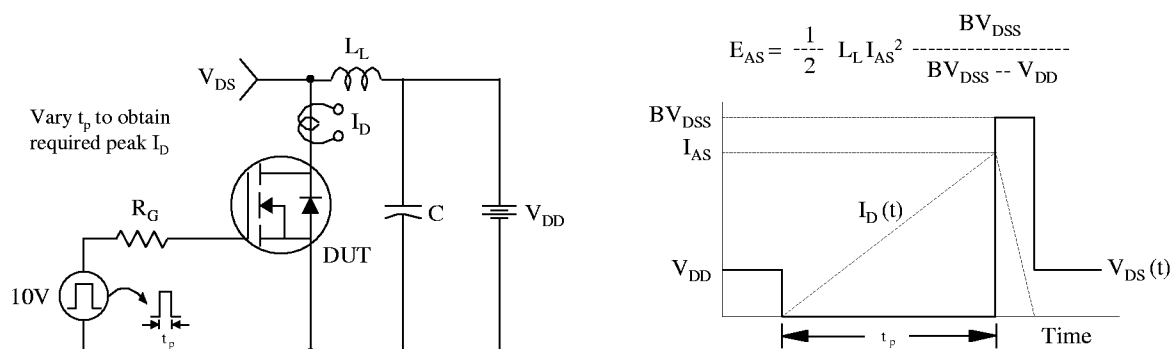
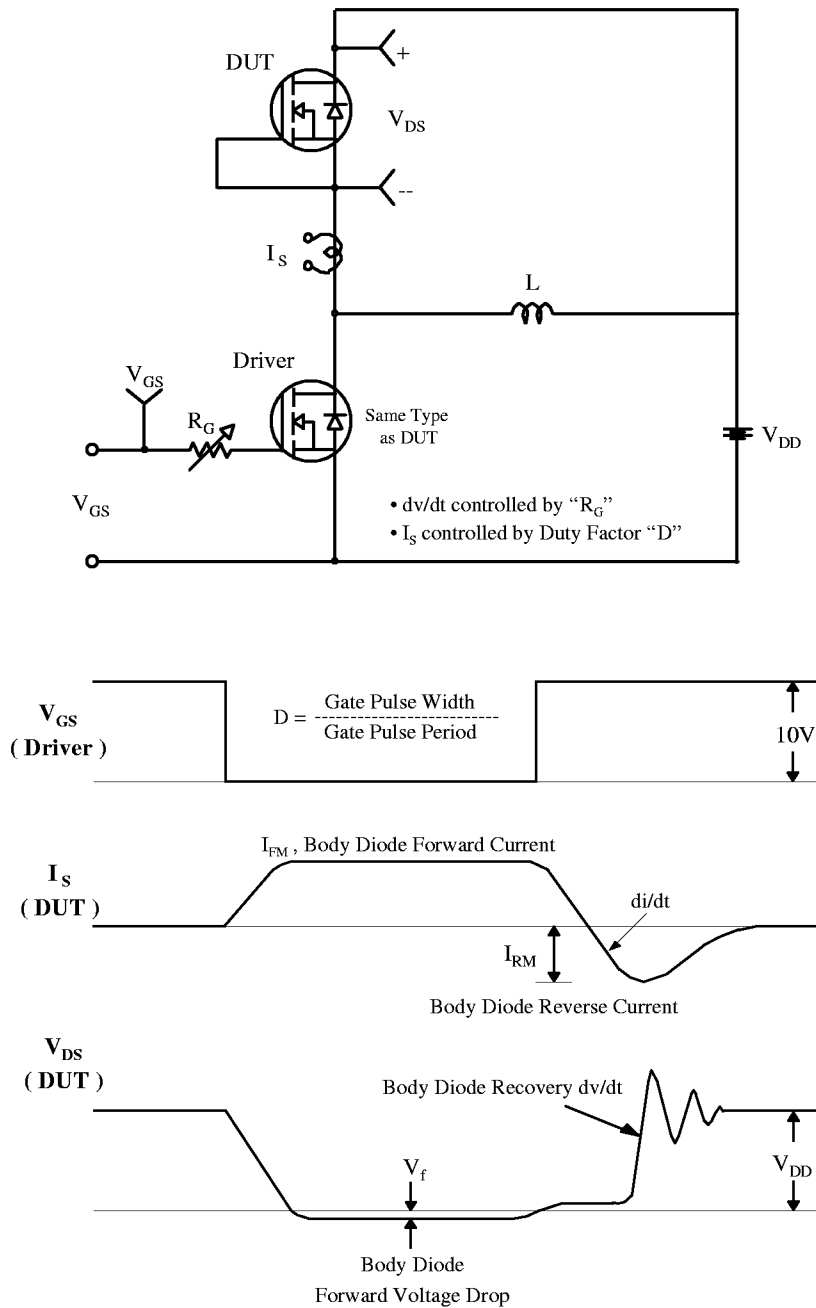
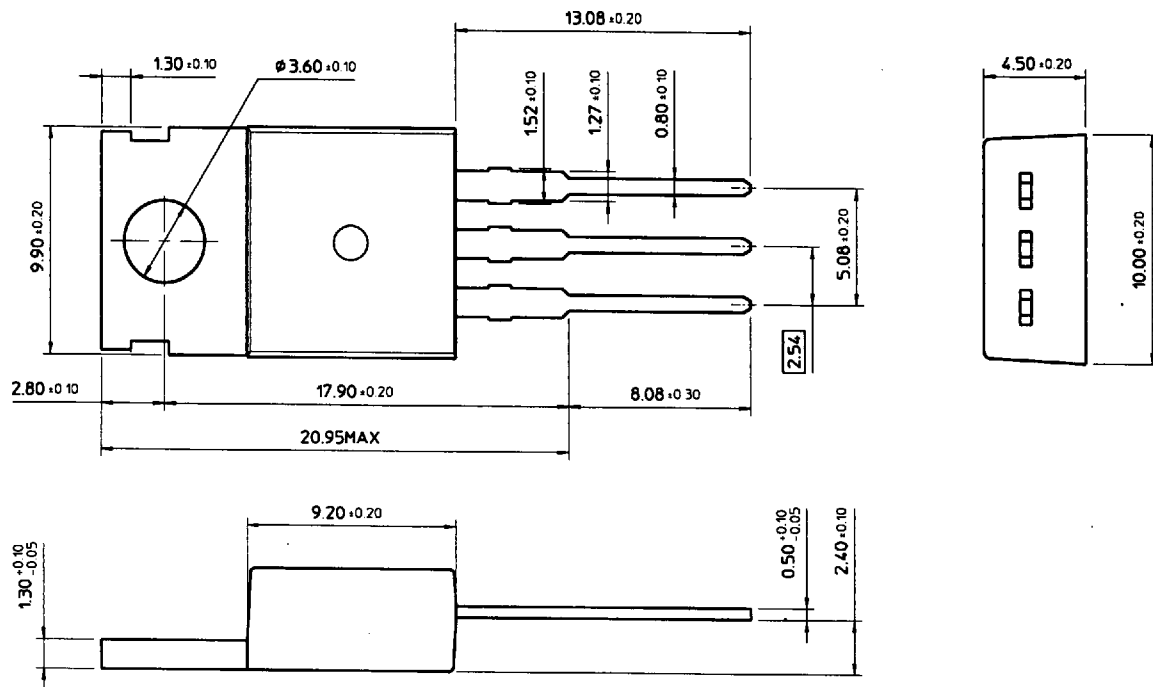


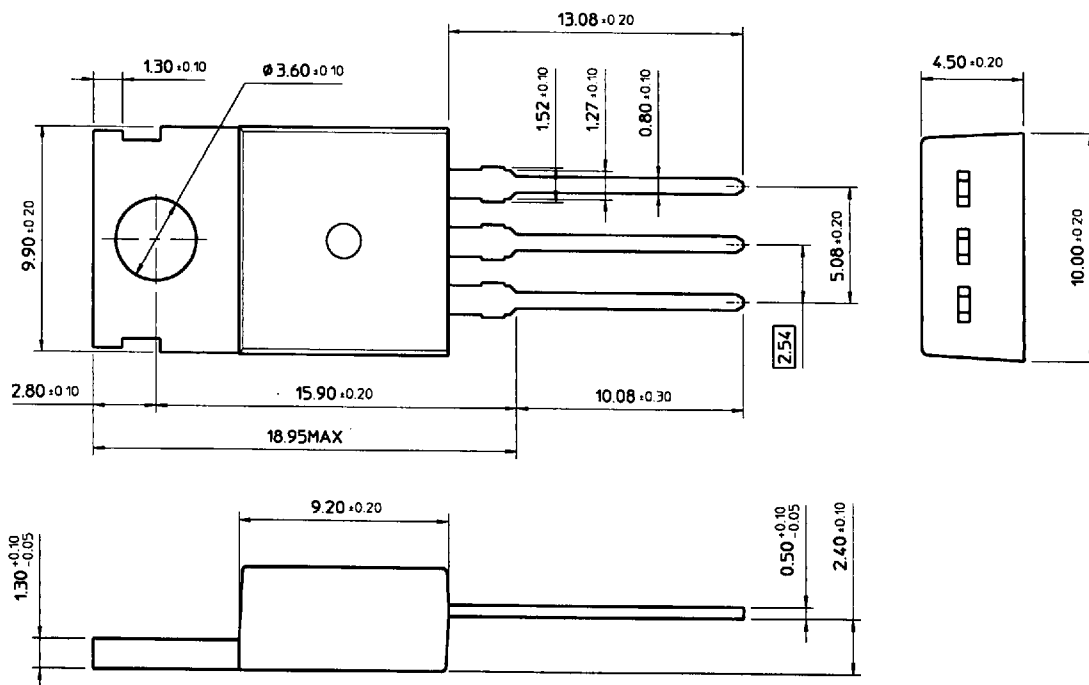
Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



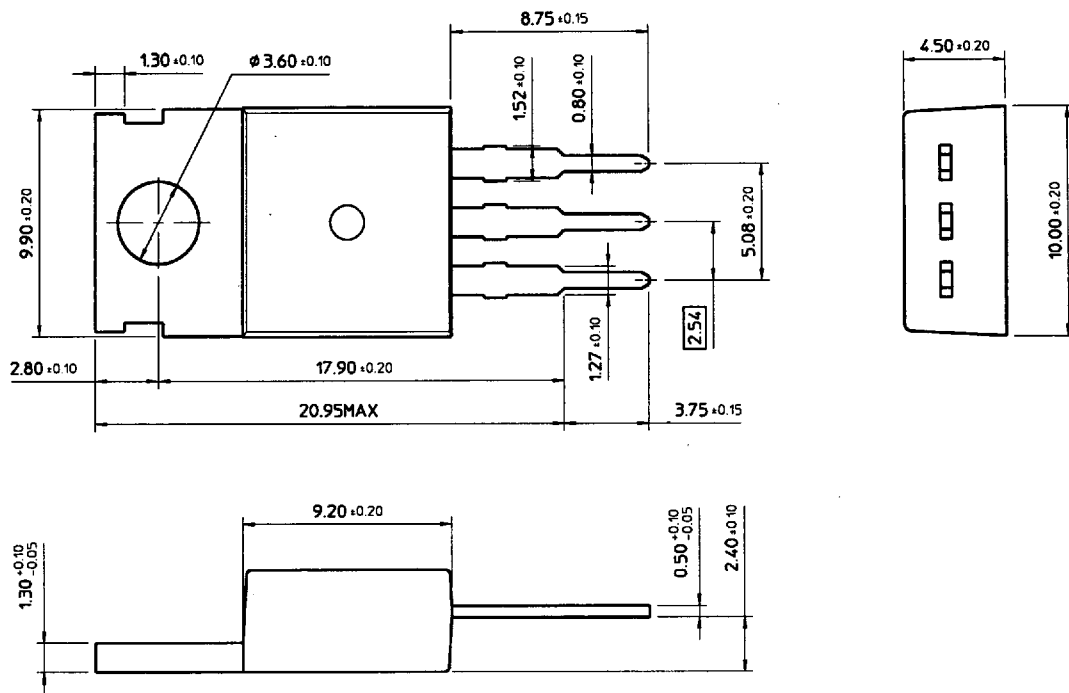
TO-220 (1)



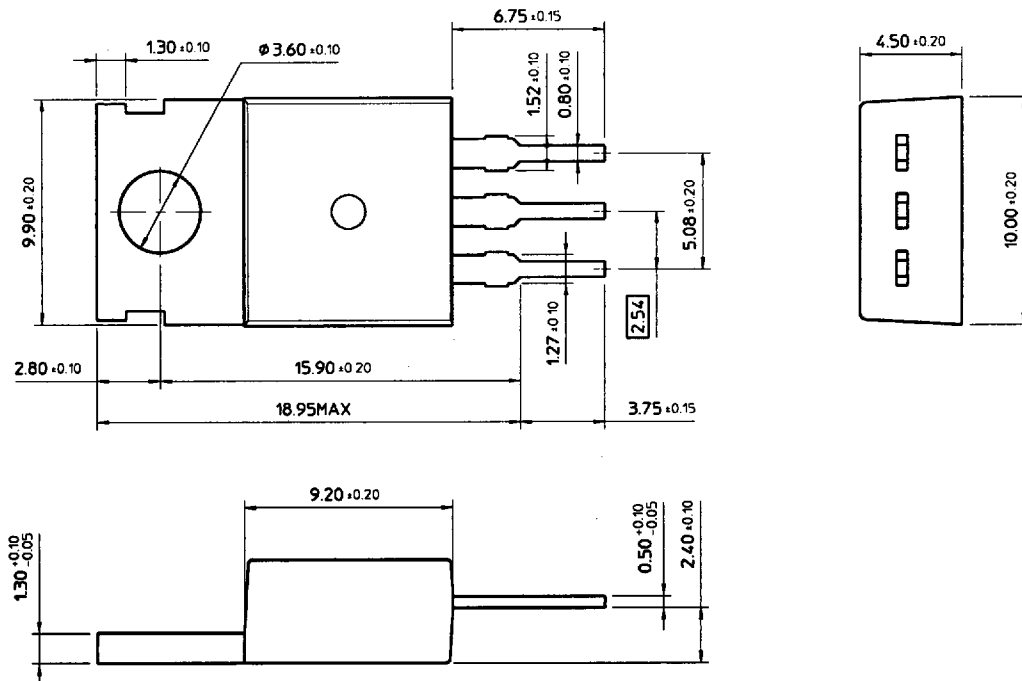
TO-220 (2)



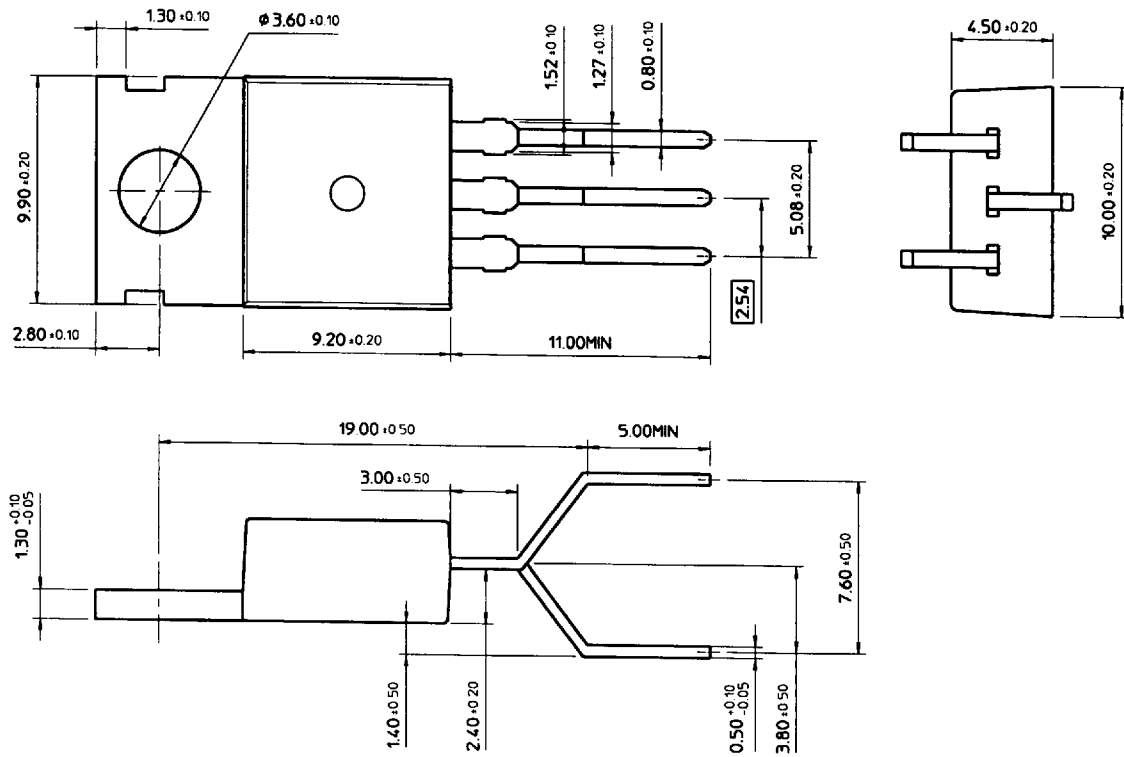
TO-220 (3)



TO-220 (4)



T0-220 (5)



NOTE